

Silicon Diode

BYV29F-300

300V/9A

DATASHEET

OEM – Philips

Source: Philips Databook 1999

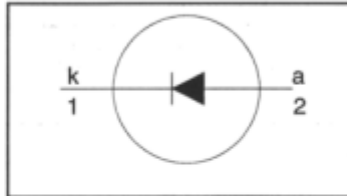
Rectifier diodes ultrafast

BYV29F series

FEATURES

- Low forward volt drop
- Fast switching
- Soft recovery characteristic
- High thermal cycling performance
- Isolated mounting tab

SYMBOL



QUICK REFERENCE DATA

$$V_R = 300 \text{ V} / 400 \text{ V} / 500 \text{ V}$$

$$V_F \leq 1.03 \text{ V}$$

$$I_{F(AV)} = 9 \text{ A}$$

$$t_{rr} \leq 60 \text{ ns}$$

GENERAL DESCRIPTION

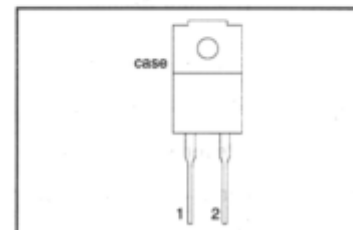
Ultra-fast, epitaxial rectifier diodes intended for use as output rectifiers in high frequency switched mode power supplies.

The BYV29F series is supplied in the conventional leaded SOD100 package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode
tab	isolated

SOD100



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
				-300	-400	-500	
V_{RRM}	Peak repetitive reverse voltage	BYV29F $T_{hs} \leq 138^\circ\text{C}$	-	300	400	500	V
V_R	Continuous reverse voltage		-	300	400	500	V
$I_{F(AV)}$	Average forward current ¹	square wave; $\delta = 0.5$; $T_{hs} \leq 90^\circ\text{C}$	-	9			A
I_{FSM}	Non-repetitive peak forward current	$t = 10 \text{ ms}$	-	100			A
		$t = 8.3 \text{ ms}$ sinusoidal; with reapplied $V_{RRM(max)}$	-	110			A
T_{stg}	Storage temperature		-40	150			$^\circ\text{C}$
T_j	Operating junction temperature		-	150			$^\circ\text{C}$

ISOLATION LIMITING VALUE & CHARACTERISTIC

$T_{hs} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	Repetitive peak voltage from both terminals to external heatsink	R.H. $\leq 65\%$; clean and dustfree	-		1500	V
C_{isol}	Capacitance from cathode to external heatsink	$f = 1 \text{ MHz}$	-	12	-	pF

¹ Neglecting switching and reverse current losses

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-hs}$	Thermal resistance junction to heatsink	with heatsink compound	-	-	5.5	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	without heatsink compound in free air.	-	55	7.2	K/W

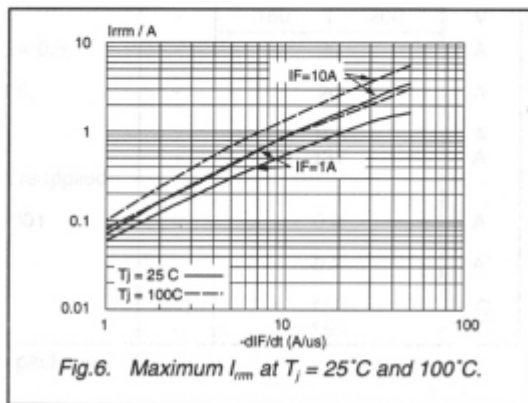
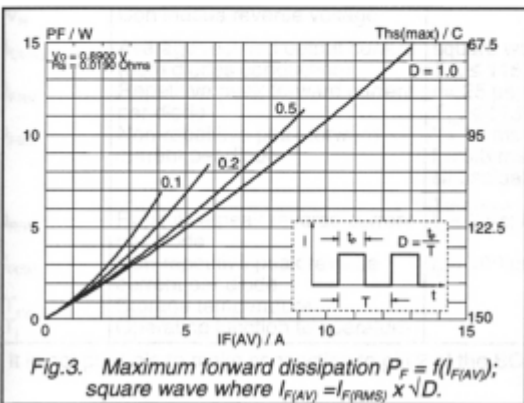
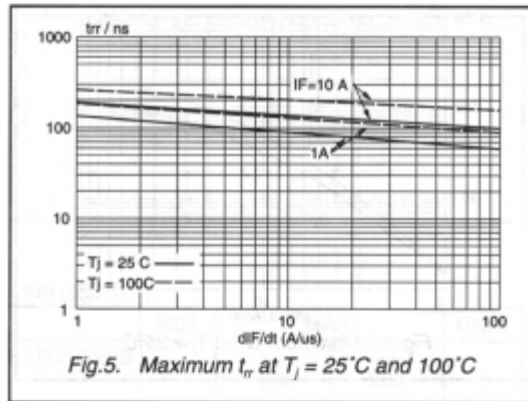
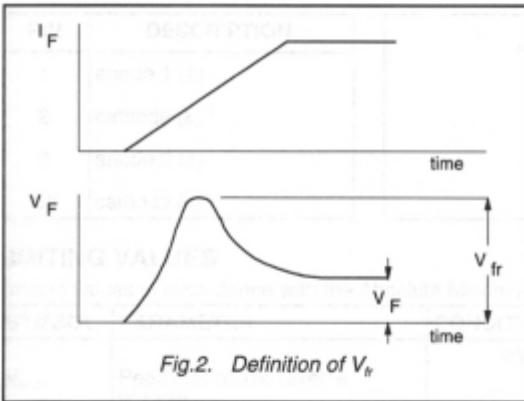
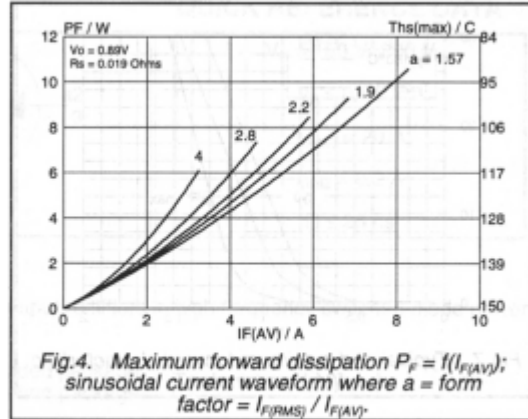
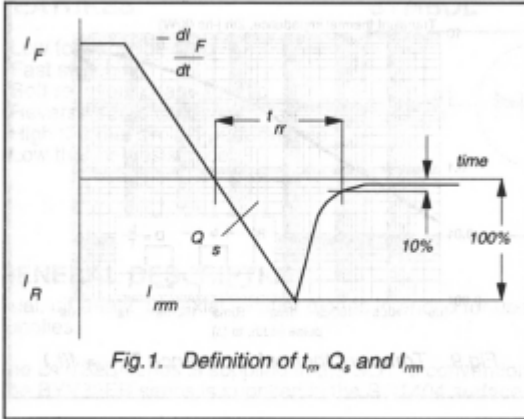
ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	Forward voltage	$I_F = 8\text{ A}$; $T_j = 150\text{ °C}$	-	0.90	1.03	V
		$I_F = 8\text{ A}$	-	1.05	1.25	V
		$I_F = 20\text{ A}$	-	1.20	1.40	V
I_R	Reverse current	$V_R = V_{RRM}$	-	2.0	50	μA
		$V_R = V_{RRM}$; $T_j = 100\text{ °C}$	-	0.1	0.35	mA
Q_s	Reverse recovery charge	$I_F = 2\text{ A}$ to $V_R \geq 30\text{ V}$; $di_F/dt = 20\text{ A}/\mu\text{s}$	-	40	60	nC
t_{rr}	Reverse recovery time	$I_F = 1\text{ A}$ to $V_R \geq 30\text{ V}$; $di_F/dt = 100\text{ A}/\mu\text{s}$	-	50	60	ns
I_{rrm}	Peak reverse recovery current	$I_F = 10\text{ A}$ to $V_R \geq 30\text{ V}$; $di_F/dt = 50\text{ A}/\mu\text{s}$; $T_j = 100\text{ °C}$	-	4.0	5.5	A
V_{fr}	Forward recovery voltage	$I_F = 10\text{ A}$; $di_F/dt = 10\text{ A}/\mu\text{s}$	-	2.5	-	V

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